Quantum coherence thermal transistors

Shanhe Su,1 Yanchao Zhang,1 Bjarne Andresen,2 Jincan Chen∗

1 Department of Physics and Jiujiang Research Institute, Xiamen University, Xiamen 361005, China.
2 Niels Bohr Institute, University of Copenhagen, Universitetsparken 5, DK-2100 Copenhagen Ø, Denmark.

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Coherent control of self-contained quantum systems offers the possibility to fabricate smallest thermal transistors. The steady coherence created by the delocalization of electronic excited states arouses nonlinear heat transports in non-equilibrium environment. Applying this result to a three-level quantum system, we show that quantum coherence gives rise to negative differential thermal resistances, making the thermal transistor suitable for thermal amplification. The results show that quantum coherence facilitates efficient thermal signal processing and can open a new field in the application of quantum thermal management devices.

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A thermal transistor, like its electronic counterpart, is capable of implementing heat flux switching and modulating. The effects of negative differential thermal resistance (NDTR) play a key role in the development of thermal transistors [1]. Classical dynamic descriptions utilizing Frenkel-Kontorova lattices conclude that nonlinear lattices are the origin of NDTR [2, 3]. Ben-Abdallah et al. introduced a distinct type of thermal transistors based on the near-field radiative heat transfer by evanescent thermal photons between bodies [4]. Joulain et al. first proposed a quantum thermal transistor with strong coupling between the interacting spins, where the competition between different decay channels makes the temperature dependence of the base flux slow enough to obtain a high amplification [5]. Zhang et al. predicted that asymmetric Coulomb blockade in quantum-dot thermal transistors would result in a NDTR [6]. Stochastic fluctuations in mesoscopic systems have been regarded as an alternate resource for the fast switching of heat flows [7]. Recent studies showed that quantum coherence exhibits the ability to enhance the efficiency of thermal converters, such as quantum heat engines [8,9] and artificial light-harvesting systems [10–12]. Interference between multiple transitions in nonequilibrium environments enables us to generate non-vanishing steady quantum coherence [13, 14]. Evidence is growing that long-lived coherence boosts the transport of energy from light-harvesting antennas to photosynthetic reaction centers [15, 16]. The question arises whether quantum interference and coherence effects could also induce nonlinear heat conduction and enhance the performance of a thermal transistor.

Scovil and Schulz-DuBois originally proposed a three-level maser system as an example of a Carnot engine and applied detailed balance ideas to obtain the maser efficiency formula [17]. Because the controlled (output) thermal flux is normally higher than the controlling (input) thermal flux, a thermal transistor is able to amplify or switch a small signal. The amplification factor must be tailored to suit specific situations. The Scovil and Schulz-DuBois maser model is not applicable for fabricating thermal transistors, owing to the fact that its amplification factor is simply a constant defined by the maser frequency relative to the pump frequency [18, 19]. However, the coherent excitation-energy transfer created by the delocalization of electronic excited states may aid in the design of powerful thermal devices. Coherent control of a three-level system (TLS) provides us a heuristic approach to better understand the prime requirements for the occurrence of anomalous thermal conduction in quantum systems.

In this paper we design a quantum thermal transistor consisting of a TLS coupled to three separate baths. The dynamics of the system is derived by considering the coupling between the two excited states. Steady-state solutions will be used to prove that the coherent transitions between the two excited states induce nonlinearity in nonequilibrium quantum systems. Further analysis shows that quantum coherence gives rise to a NDTR and helps improve the thermal amplification.

Figure 1 shows the TLS modeled by the Hamiltonian $H_S$ as

$$H_S = \sum_{i=0,1,2} \varepsilon_i |i\rangle \langle i| + \Delta(|1\rangle \langle 2| + |2\rangle \langle 1|),$$

where $\varepsilon_1$ ($\varepsilon_2$) gives the energy level of the excited states in the molecules $|1\rangle$ ($|2\rangle$), $\varepsilon_0$ denotes the energy of the ground state $|0\rangle$ and is set to zero, and $\Delta$ describes the excitonic coupling between states $|1\rangle$ and $|2\rangle$. For the models of biological light reactions, $\Delta$ occurs naturally as a consequence of the intermolecular forces between two proximal optical dipoles [12, 20]. In the presence of the dipole-dipole interaction, the optically excited states become coherently delocalized. $|+\rangle = \cos \theta |1\rangle + \sin \theta |2\rangle$ and $|-\rangle = \sin \theta |1\rangle - \cos \theta |2\rangle$ are the usual eigenstates.

∗ jcchen@xmu.edu.cn
the two excited states and the dephasing bath becomes not only decoherence but also relaxation [21]. The absorption of a photon from the emitter (E) causes an excitation transfer from the ground state |0⟩ to the state |1⟩, whereas phonons are emitted into the base (B) by the transitions between |1⟩ and |2⟩. The cycle is closed by the transition between |2⟩ and |0⟩, and the rest of the energy is released as a photon to the collector (C). The Hamiltonians of the emitter, collector, and base are

\[ H_i = \sum_k \omega_{ik} a_{ik}^\dagger a_{ik} \] (i = E, C, and B),

where \( a_{ik}^\dagger \) (\( a_{ik} \)) refers to the creation (annihilation) operator of the bath mode \( \omega_{ik} \). The TLS couples to the emitter and the collector, each constituted of harmonic oscillators, via coupling constants \( g_{Ek} \) and \( g_{Ck} \) in the rotating wave approximation, where the corresponding Hamiltonians are formally written as

\[ H_{SE} = \sum_k \left( g_{Ek} a_{Ek}^\dagger |0\rangle \langle 1| + \text{h.c.} \right) \]

and

\[ H_{SC} = \sum_k \left( g_{Ck} a_{Ck} |0\rangle \langle 2| + \text{h.c.} \right), \]

respectively. The output of the Scovil–Schulz-DuBois maser is a radiation field with a particular frequency, provided there is population inversion between levels \( \varepsilon_1 \) and \( \varepsilon_2 \). In this study, the two excited states are coupled with a thermal reservoir, namely, the base. The interaction Hamiltonian of the system with the base is described by

\[ H_{SB} = (|1\rangle \langle 1| - |2\rangle \langle 2|) \sum_k g_{Bk} \left( a_{Bk}^\dagger + a_{Bk} \right). \] (2)

For a finite coupling \( \Delta \), the base modeled by Eq. (2) induces not only decoherence but also relaxation [21]. The counterintuitive effect of the energy exchange between the two excited states and the dephasing bath becomes evident when the system operator coupled to the base is replaced by

\[ |1\rangle \langle 1| = \cos \theta \cos \theta |+\rangle \langle +| + \sin \theta \sin \theta |\rangle \langle | \]

\[ + \sin \theta \cos \theta (|+\rangle \langle | + |\rangle \langle +|) \] (3)

and

\[ |2\rangle \langle 2| = \sin \theta \sin \theta |+\rangle \langle +| + \cos \theta \cos \theta |\rangle \langle | \]

\[ - \cos \theta \sin \theta (|+\rangle \langle | + |\rangle \langle +|) \]. \] (4)

The first two operators in |1⟩ ⟨1| and |2⟩ ⟨2| describe the pure dephasing of a two-level system, whereas the third term leads to the energy exchange between the system and the base with an effective coupling proportional to the product \( \sin \theta \cos \theta \), i.e.,

\[ H_{SB-eff} = 2 \sin \theta \cos \theta (|+\rangle \langle | + |\rangle \langle +|) \sum_k g_k \left( a_k + a_k^\dagger \right). \] (5)

In reality, the TLS can be realized in the photosynthesis process. The pumping light, taking the sunlight photons for example, is considered the high temperature emitter. The collector is formed by the surrounding electromagnetic environment which models energy transfer to the reaction center. The base provides the phonon modes coupled with the excited states.

The TLS becomes irreversible due to the interaction with its surrounding environment. Using the Born-Markov approximation, which involves the assumptions that the environment is time independent and the environment correlations decay rapidly in comparison to the typical time scale of the system evolution [22], we get the quantum dynamics of the system in \( h = 1 \) units, i.e.,

\[ \frac{d\rho}{dt} = -i[H_S, \rho] + D_E[\rho] + D_B[\rho] + D_C[\rho]. \] (6)

The operators \( D_i[\rho] \) (i = E, B, and C) denote the dissipative Lindblad superoperators associated with the emitter, base, and collector (Supplementary Eq. (S-1)), which take the form

\[ D_i[\rho] = \sum_v \gamma_i(v) \left[ A_i(v) \rho A_i^\dagger(v) - \frac{1}{2} \left\{ \rho, A_i^\dagger(v) A_i(v) \right\} \right], \] (7)

where \( v = \varepsilon - \varepsilon' \) is the energy difference between two arbitrary eigenvalues of \( H_S \), and \( A_i(v) \) is the jump operator associated with the interaction between the system and bath \( i \). Considering a quantum bath consisting of harmonic oscillators, we have the decay rate \( \gamma_i(v) = T_i(v) n_i(v) \) for \( v < 0 \) and \( \gamma_i(v) = T_i(v) [1 + n_i(v)] \) for \( v > 0 \), where \( T_i(v) \) labels the decoherence rate and is related to the spectral density of the bath, and \( T_i \) is the temperature of bath \( i \). The thermal occupation number in a mode is written as \( n_i(v) = 1/[e^{v/(k_B T_i)} - 1] \). The Boltzmann constant \( k_B \) is set to unity in the following.

The steady-state populations and coherence of the open quantum system are obtained by setting the left-hand side of Eq. (6) equal zero. Then the steady state energy fluxes are determined by the average energy going through the TLS, i.e.,

\[ \dot{E}(\infty) = \sum_{i=E,C,B} \text{Tr}[H_SD_i(\rho(\infty))] = J_E + J_C + J_B = 0 \] (8)
which complies with the 1st law of thermodynamics. The heat fluxes \( J_E, J_C, \) and \( J_B \) are defined with respect to their own dissipative operators. Thus,

\[
J_E = -\Gamma_E (\varepsilon_1) (n_E + 1) \left[ \varepsilon_1 \left( \rho_1 - \frac{n_E}{n_E + 1} \rho_0 \right) + \Delta \mathcal{R} (\rho_{12}) \right] = J_{E1} + J_{E2},
\]

\[
J_C = -\Gamma_C (\varepsilon_2) (n_C + 1) \left[ \varepsilon_2 \left( \rho_2 - \frac{n_C}{n_C + 1} \rho_0 \right) + \Delta \mathcal{R} (\rho_{12}) \right] = J_{C1} + J_{C2},
\]

and

\[
J_B = -\Gamma_B (\omega) \sin^2 2\theta (2n_B + 1) \left[ \frac{\varepsilon_1 - \varepsilon_2}{2} (\rho_{11} - \rho_{22}) + \frac{\sqrt{(\varepsilon_1 - \varepsilon_2)^2 / 4 + \Delta^2}}{2n_B + 1} + 2 \Delta \mathcal{R} (\rho_{12}) \right] = J_{B1} + J_{B2}.
\]

The three heat fluxes are no longer linear functions of the rate of the spontaneous emission, indicating that the symmetric property is closely related to the base induced coherence of the excited states. In Eqs. (9) – (11), each heat flux is divided into two categories. The terms \( J_{ij} (i = E, C, B) \) are connected to the coherence in the local basis, i.e., \( \mathcal{R} (\rho_{12}) \) (the real part of \( \rho_{12} \)). \( J_{ii} \) is the remainder components depending on the populations of the TLS.

The thermodynamics of a TLS was originally proposed by Scovil and Schulz-DuBois [17]. Boukobza et al. obtained the Scovil–Schulz-DuBois master efficiency formula when the TLS was operated as an amplifier [18, 23, 24]. The efficiency of the amplifier is defined as the ratio of the output energy to the energy extracted from the hot reservoir [25]. In a nonequilibrium steady state, the efficiency is a fixed value which equals \( 1 - (\varepsilon_2 - \varepsilon_0) / (\varepsilon_1 - \varepsilon_0) \), because all heat fluxes are linear functions of the same rate of excitation. However, a thermal transistor is a thermal device used to amplify or switch the thermal currents at the collector and the emitter via a small change in the base heat flux or the base temperature. Nonlinearity is the essential element needed to give rise to such thermal amplification. For the purpose of flexible control of the thermal currents, the characteristic functions of the TLS should not entirely depend upon the energy level structure of the TLS.

A thermal amplifier requires a transistor with a high amplification factor \( \alpha_{E/C} \), which is defined as the instantaneous rate of change of the emitter or collector heat flux to the heat flux applied at the base. The quantum thermal transistor has fixed emitter and collector temperatures \( T_E \) and \( T_C \) (\( T_E > T_C \)), respectively. The fluxes \( J_E \) and \( J_C \) are controlled by \( J_B \), which can be adjusted by the base temperature \( T_B \). Then the amplification factor \( \alpha_{E/C} \) explicitly reads

\[
\alpha_{E/C} = \frac{\partial J_{E/C}}{\partial J_B}.
\]

Comparison of the slopes of the thermal currents is the key parameter to find out whether the amplification effect exists. When \( |\alpha_{E/C}| > 1 \), a small change in \( J_B \) stimulates a large variation in \( J_E \) or \( J_C \) and the thermal transistor effect appears. This implies that a small change of the heat flux signal of the base would lead to noticeable changes of the energy flowing through the emitter and collector.

We consider heat fluxes from the baths into the TLS as positive. As \( T_E \) and \( T_C \) are fixed values and \( T_B \) is adjustable, the thermal conductances of the three terminals are defined as

\[
\sigma_i = -\frac{\partial J_i}{\partial T_B} = \sigma_{i1} + \sigma_{i2},
\]

where \( \sigma_{ij} = -\frac{\partial J_i}{\partial T_E} (i = E, C, B; j = 1, 2) \), \( \sigma_{i1} \) are the thermal conductances with respect to the spontaneous emission, and \( \sigma_{i2} \) are the thermal conductances relying on the coherence \( \mathcal{R} (\rho_{12}) \). Using Eq. (13), the amplification factor in Eq. (12) can be recast in terms of \( \sigma_E \) and \( \sigma_C \), i.e.,

\[
\alpha_{E/C} = -\frac{\sigma_{E/C}}{\sigma_C + \sigma_E}.
\]

The absolute value of the amplification factor \( |\alpha_{E/C}| > 1 \) implies that one of the thermal conductances is negative, i.e., \( \sigma_C < 0 \) or \( \sigma_E < 0 \). This means that there exists a NDTR, and consequently, the TLS can behave as a thermal transistor by controlling the heat flow in analogy to the usual electric transistor.

In the following section, we need to explore the extent to which the quantum nature of the TLS affects the thermal transistor. The formalism obtained here will allow us to access how coherences can lead to a NDTR and an enhancement of the amplification factor. To do so, the thermal conductances and temperatures of the three baths are recast in units of \( \Delta \). In the wide-band approximation, we write the decoherence rates of the three terminals as \( \Gamma_i (v) = \Gamma_i \) and the dephasing rate of the base as \( \gamma_B (0) = \gamma_0 \).

Figure 2(a) shows the thermal conductances \( \sigma_i \) of each terminal as functions of the base temperature \( T_B \), \( |\sigma_E| \), \( \sigma_C \), and \( \sigma_B \) decrease with \( T_B \) at low temperature and become constant as \( T_B \) approaches \( T_E \). As expected, \( \sigma_B \) remains lower than \( |\sigma_E| \) and \( \sigma_C \) over the whole range. A tiny change of the base heat flux \( J_B \) or temperature \( T_B \) is able to dramatically change the emitter and collector thermal flows \( J_E \) and \( J_C \), leading to a noticeable amplification effect. Similar to the decomposition of the thermal fluxes, each thermal conductance can be divided
into two separate parts. Figures 2 (b) and (c) display the thermal conductances \( \sigma_1 \) pertaining to the population distributions and to the coherence contributed thermal conductances \( \sigma_2 \) varying with the base temperature \( T_B \). \( \sigma_21 \), \( \sigma_22 \), and \( \sigma_2B \) share a magnitude close to each other, indicating that it is unlikely to create an autonomous thermal amplifier without coherence. Quantum coherence \( \mathbb{R} \{ \rho_{12} \} \) exists [Fig. 2(d)], allowing us to modify the thermodynamic behavior through the quantum control. For the two thermal conductances \( \sigma_{B1} \) and \( \sigma_{B2} \) of the base, \( \sigma_{B1} \) > 0 [Fig. 2 (b)], whereas \( \sigma_{B2} \) originating from the coherence is negative [Fig. 2(c)], ensuring that we achieve a vanishing \( \sigma_B \) [Fig. 2(a)]. Such a phenomenon makes large thermal amplifications possible.

The curves of the amplification factors \( \alpha_E \) and \( \alpha_C \) as functions of the base temperature \( T_B \) are illustrated in Fig. 3. The amplification factors \( \alpha_E \) and \( \alpha_C \) are clearly greater than 1 over a large range of \( T_B \). As seen from Eq. (14), these effects result from \( \sigma_E < 0 \), which is similar to the property of some electrical circuits and devices where an increase in voltage across the overall assembly results in a decline in electric current through it, i.e., negative differential conductance. Specifically, Fig. 3 shows that the amplification factors diverge at \( T_B = 135.3\Delta \) due to the fact that the thermal conductance of the base \( \sigma_B = 0 \), induced by the quantum coherence. Under these conditions, an infinitesimal change in \( J_B \) makes a considerable difference in \( J_E \) and \( J_C \).

Figures 4 and 5 reveal the influences of the decoherence rate \( \Gamma_B \) and the dephasing rate of the base \( \gamma_0 \) on the performance of the thermal transistor. The base temperature \( T_B = \Delta/0.015 \), while the values of other parameters are the same as those used in Fig. 2. The amplification factor \( \alpha_C \) increases as \( \Gamma_B \) increases in the small-\( \Gamma_B \) regime \( (\Gamma_B < 1.287\Delta) \), but it decreases as \( \Gamma_B \) increases in the large-\( \Gamma_B \) regime \( (\Gamma_B > 1.287\Delta) \), while \( \alpha_C \) tends to divergence for \( \Gamma_B \to 1.287\Delta \). The amplification factor \( \alpha_E \) as a function of \( \Gamma_B \) has opposite signs. The decoherence rate \( \Gamma_B \) is an important parameter for building a desirable amplifier. As illustrated in Figure 4(b), the thermal conductance \( \sigma_B \) of the base is the sum of \( \sigma_{B1} \) and \( \sigma_{B2} \). Once again, we observe that \( \sigma_{B1} \) is always positive, while the thermal conductance relevant to the coherence effect \( \sigma_{B2} < 0 \) leading to a cancellation of the sum when \( \Gamma_B \to 1.287\Delta \). For the same reason, the amplification factors diverge at \( \Gamma_B \to 1.287\Delta \) when \( \sigma_B = 0 \).

Coherence is maintained in a nonequilibrium steady state even in the presence of the dephasing bath. However, a large dephasing rate has a deleterious effect on the characteristics of the TLS thermal transistor [Fig. 5(b)]. Figure 5(a) shows that the absolute value \( |\rho_{12}| \) and the real part \( \mathbb{R} \{ \rho_{12} \} \) of coherence are monotonically decreasing functions of \( \gamma_0 \), the decoherence rate of the base. The pure-dephasing bath acting on the TLS induces the loss of steady coherence, yielding smaller \( \alpha_E/\alpha_C \).

In summary, we build a TLS to analyze the effects of the dipole–dipole interaction and the dephasing on the energy transfer processes in a thermal transistor. The coupling between the two excited states of the TLS is capable of generating steady coherence in a nonequilibrium environment, making the thermal fluxes behave nonlinearly. The coherence, at the same time, gives rise to
Figure 5. (a) The absolute value and the real part of coherence, $|\rho_{12}|$ and $\Re[\rho_{12}]$, versus the dephasing rate of the base $\gamma_0$. (b) The amplification factors $\alpha_E$ (solid line) and $\alpha_C$ (dashed line) versus the dephasing rate of the base $\gamma_0$.

NTDR of the base. Quantum coherence enables the thermal flow through the collector and emitter to be controlled by a small change in the heat flux through the base. Such a thermal transistor can amplify a small input signal as well as direct heat to flow preferentially in one direction. The thermal transistor effect can be significantly improved by optimizing the base temperature and coherence rate or reducing the dephasing rate.

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